

IN THE SPECIFICATION:

Please amend paragraph 31 as follows:

B₁
[31] FIG. 2A shows a process of manufacturing a metallic film ~~consisting of such as~~
~~Pt, Au, Cu, Al, Ni, Ag, Ir, Pd, Ti, Ru, Ta, W, Os, or Rh,~~ comprising giant single crystal grains
according to one embodiment of the present invention.

Please amend paragraph 32 as follows:

[32] Referring to FIG. 2A, a metallic film 201 for driving a electronic device or
processing a signal is deposited on a substrate 200. The deposition process is executed
under an atmosphere comprising an inert gas, i.e., argon, and a desired additive gas ~~such~~
~~as O₂, N₂+O₂, N₂O, Cl, or N₂~~ to change surface energy, grain boundary energy or internal
strain energy of the metallic film.

Please amend paragraph 43 as follows:

B₂
43
[34] FIG. 3B shows a device fabricated on the metallic film consisting of a giant
single crystal grains produced according to the present invention using the patterning
technique, specifically a shadow mask.